

FCP11N60N / FCPF11N60NT N-Channel MOSFET 600V, **10.8A**, **0.299**Ω

Features

- $R_{DS(on)} = 0.255\Omega$ (Typ.)@ $V_{GS} = 10V$, $I_D = 5.4A$
- Ultra Low Gate Charge (Typ. Qg = 27.4nC)
- · Low Effective Output Capacitance
- 100% Avalanche Tested
- · RoHS Compliant



Description

The SupreMOS MOSFET, Fairchild's next generation of high voltage super-junction MOSFETs, employs a deep trench filling process that differentiates it from preceding multi-epi based technologies. By utilizing this advanced technology and precise process control, SupreMOS provides world class Rsp, superior switching performance and ruggedness.

This SupreMOS MOSFET fits the industry's AC-DC SMPS requirements for PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

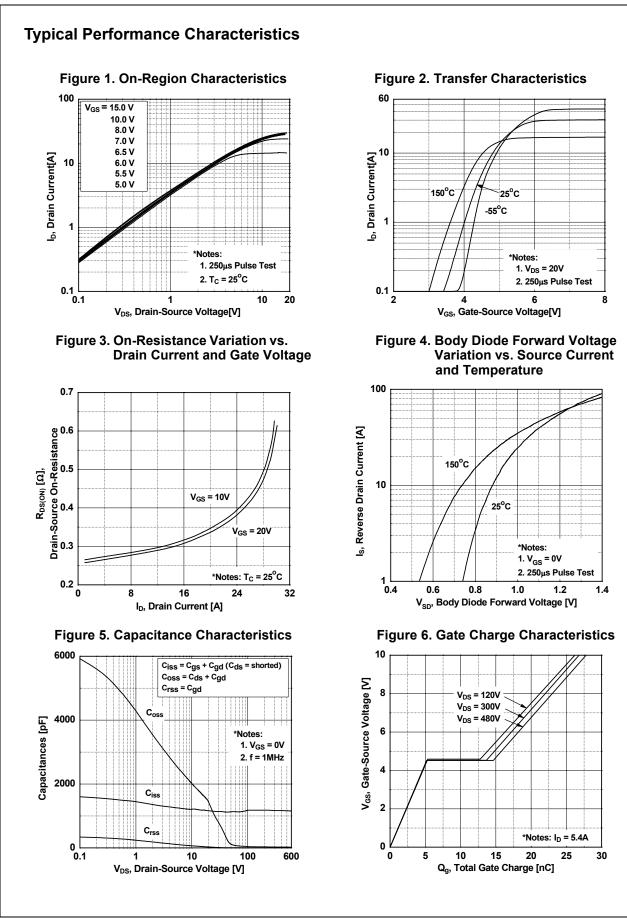
Symbol		Parameter		FCP11N60N	FCPF11N60NT	Units	
V _{DSS}	Drain to Source Voltage	600		V			
V _{GSS}	Gate to Source Voltage	Gate to Source Voltage				V	
I _D	Drain Current	-Continuous (T _C = 25 ^o C)		10.8	10.8*	•	
		-Continuous (T _C = 100 ^o C)		6.8	6.8*	A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	32.4	32.4*	Α	
E _{AS}	Single Pulsed Avalanche Ener	201.7		mJ			
I _{AR}	Avalanche Current				3.7		
E _{AR}	Repetitive Avalanche Energy				0.94		
du/dt	MOSFET dv/dt Ruggedness		100		V/ns		
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	20		V/ns	
P _D	Power Dissipation	$(T_{\rm C} = 25^{\rm o}{\rm C})$		94.0	32.1	W	
		- Derate above 25 ^o C		0.75	0.26	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 t	o +150	°C	
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			:	300	°C	

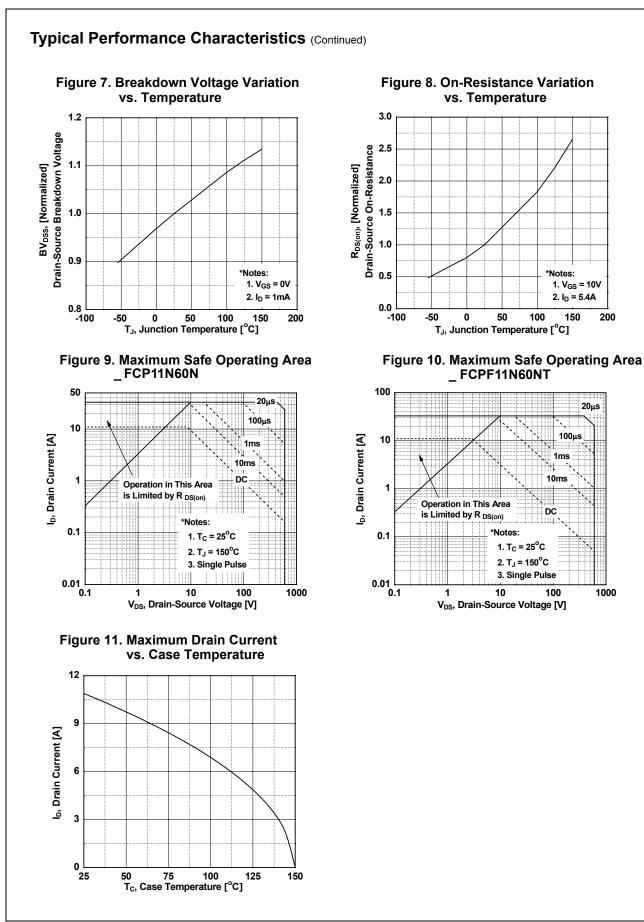
Thermal Characteristics

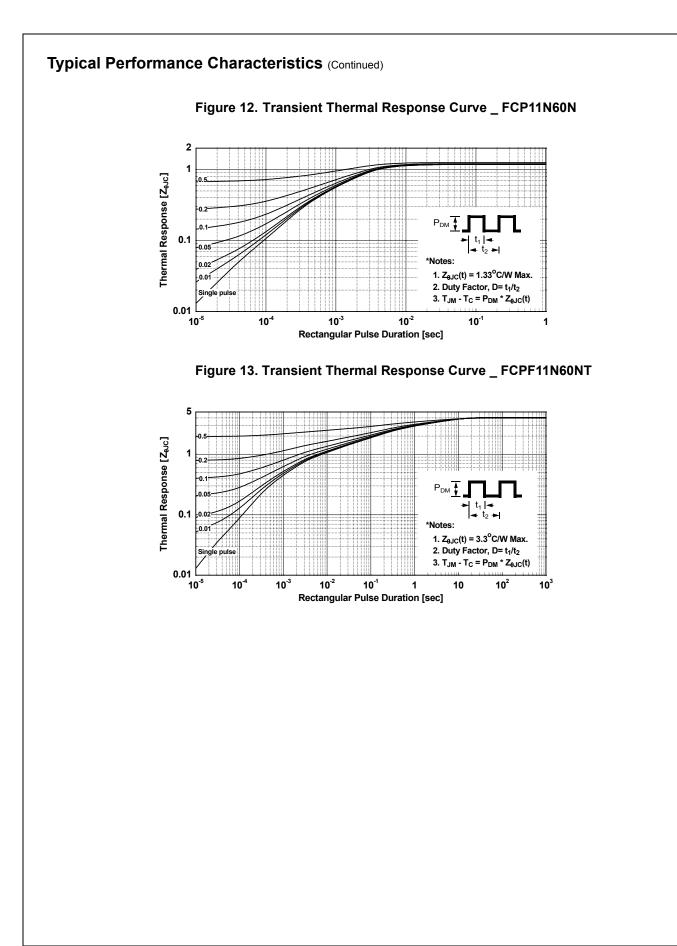
Symbol	Parameter		FCPF11N60NT	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	1.33	3.9	
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink (Typical)	0.5	0.5	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	62.5	62.5	

August 2009

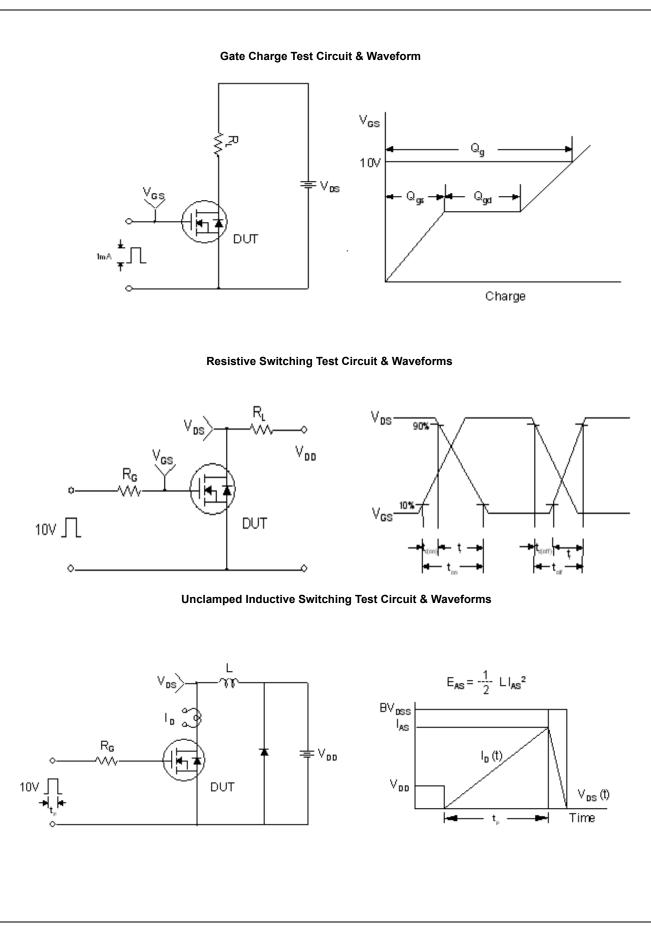
-		Device	Packag	je	Reel Size	Таре	e Width		Quantit	у
		TO-22	0	-		-		50		
FCPF11N	160NT	FCPF11N60NT	TO-220)F	-		-		50	
Electrica	l Char	acteristics T _c =	25°C unless	otherwise	noted					
Symbol		Parameter		Test Conditions		Min.	Тур.	Max.	Units	
Off Charad	cteristic	S								
BV _{DSS}	Drain to	n to Source Breakdown Voltage		$l_{\rm D} = 1 m A$	A, V _{GS} = 0V, T _C =	25⁰C	600	-	-	V
ΔBV _{DSS}		8		$I_D = 1$ mA, Referenced to 25°C						
ΔT_{J}	Breakdown Voltage Temperature Coefficient					-	0.73	-	V/°C	
	7			V _{DS} = 480V, V _{GS} = 0V		-	-	10		
DSS Zero Gate Voltage Drain Current		ent	$V_{DS} = 480V, V_{GS} = 0V, T_C = 125^{\circ}C$			-	-	100	μA	
I _{GSS}	Gate to	Gate to Body Leakage Current		$V_{GS} = \pm 3$	30V, V _{DS} = 0V		-	-	±100	nA
	toriotio	•								
On Charac						1		1		
V _{GS(th)}		nreshold Voltage			_{DS} , I _D = 250μA		2.0	-	4.0	V
R _{DS(on)}		Prain to Source On Res	sistance		0V, I _D = 5.4A		-	0.255	0.299	Ω
9 _{FS}	Forward	orward Transconductance		V _{DS} = 40V, I _D = 5.4A			-	13.5	-	S
Dynamic (Characte	eristics								
C _{iss}	1	Input Capacitance Output Capacitance Reverse Transfer Capacitance					-	1130	1505	pF
C _{oss}				──V _{DS} = 100V, V _{GS} = 0V f = 1MHz		-	45	60	pF	
C _{rss}						-	3	5	pF	
C _{oss}		t Capacitance		V _{DS} = 380V, V _{GS} = 0V, f = 1MHz		-	25	-	pF	
C _{oss} eff.		ive Output Capacitance			$V_{\rm DS} = 0V$ to 480V, $V_{\rm GS} = 0V$		-	130	_	pF
Q _{g(tot)}		Gate Charge at 10V o Source Gate Charge		$V_{\rm DS}$ = 380V, I _D = 5.4A,		-	27.4	35.6	nC	
Q_{gs}						-	4.9	-	nC	
				V _{GS} = 10V				8.8	_	nC
Q _{gd}		o Drain "Miller" Charge		(Note 4)		-		-		
ESR	Equivalent Series Resistance (G-S)		(G-S)	Drain Open				2.0		Ω
Switching	Charac	teristics								
t _{d(on)}		n Delay Time		$V_{DD} = 380V, I_D = 5.4A$ $R_G = 4.7\Omega$ (Note 1)			-	13.6	37.2	ns
t _r		n Rise Time				-	9.1	28.2	ns	
t _{d(off)}		f Delay Time				_	-	42.0	94.0	ns
t _f		f Fall Time				(Note 4)	-	10.0	30.0	ns
1						(********)				
Drain-Sou	rce Dio	de Characteristic	S							
l _S	Maximum Continuous Drain to Source Dio		Source Diod	de Forward Current		-	-	10.8	Α	
I _{SM}	Maximu	Maximum Pulsed Drain to Source Diode F		orward Current		-	-	32.4	Α	
V _{SD}	Drain to	ain to Source Diode Forward Voltage		V _{GS} = 0V, I _{SD} = 5.4A		-	-	1.2	V	
t _{rr}	Reverse	e Recovery Time		$V_{GS} = 0V, I_{SD} = 5.4A$ $dI_F/dt = 100A/\mu s$		-	268	-	ns	
Q _{rr}	Reverse	e Recovery Charge				-	3.1	-	μC	





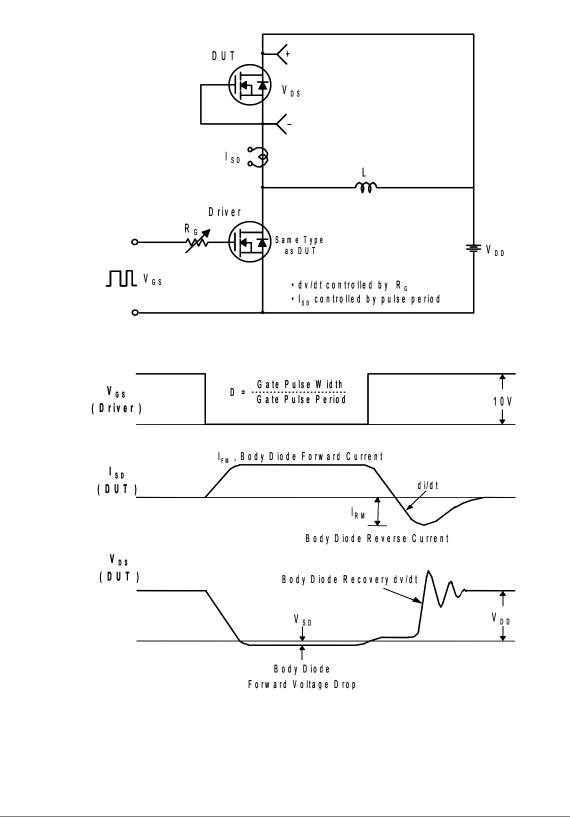


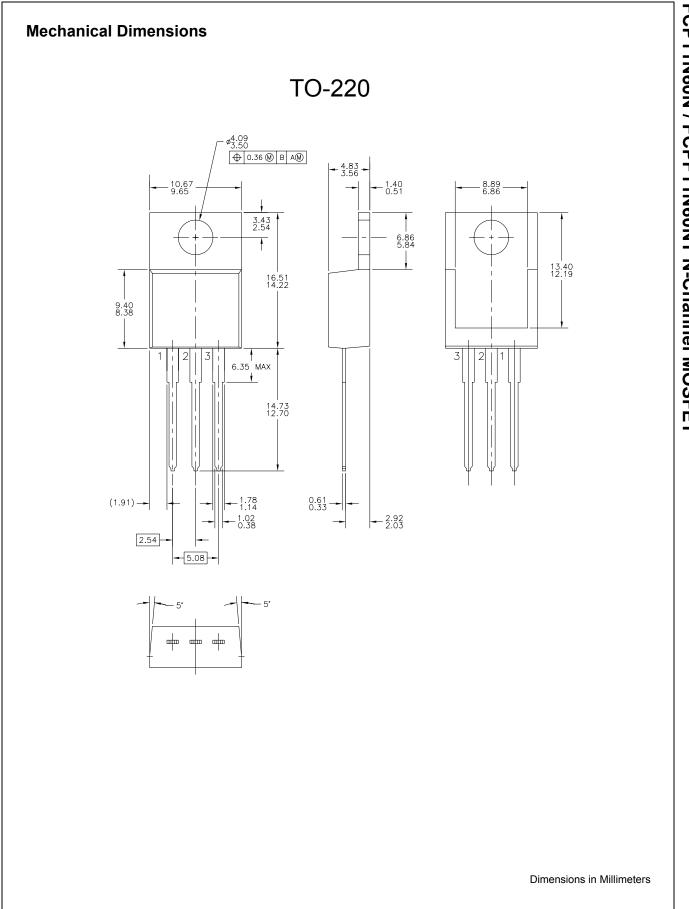


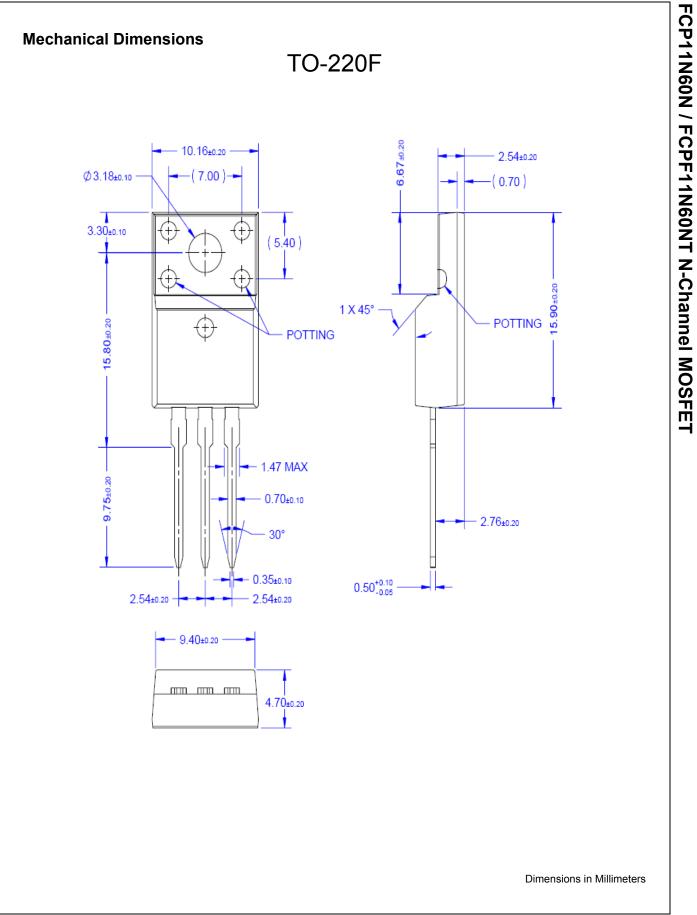


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